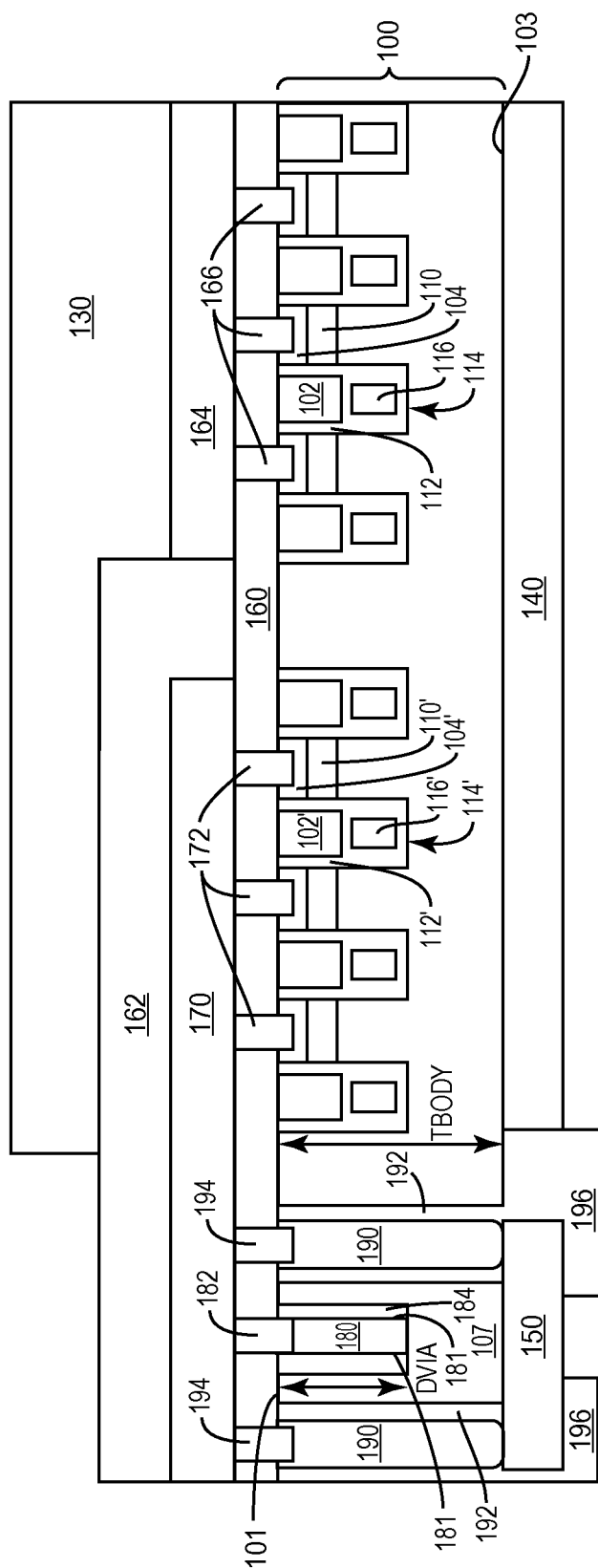


# FIGURE 1



## FIGURE 2

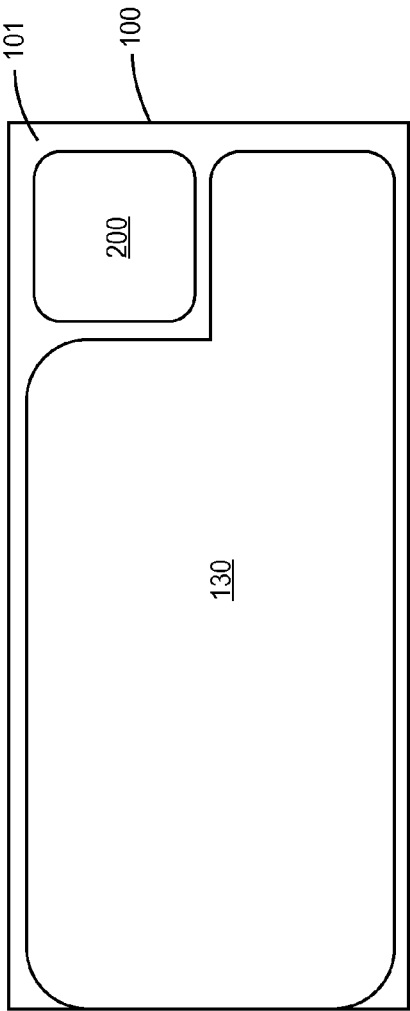


FIGURE 3A

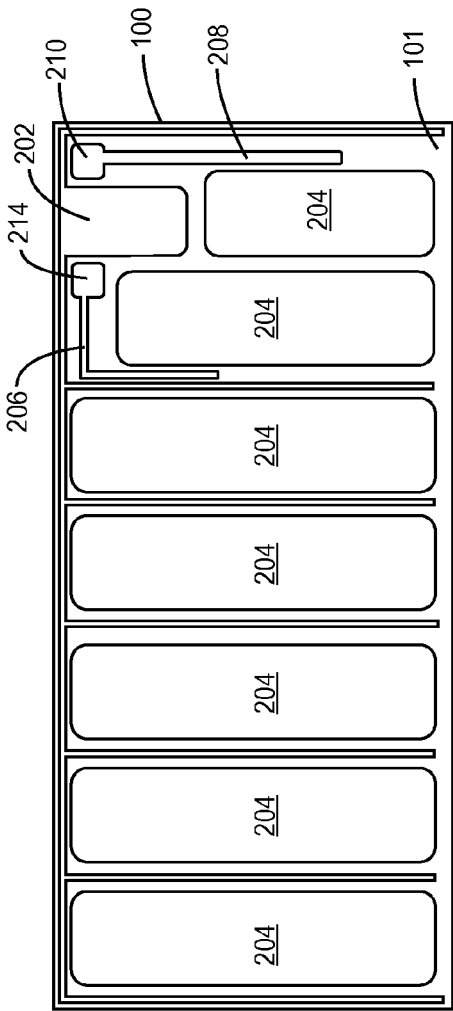
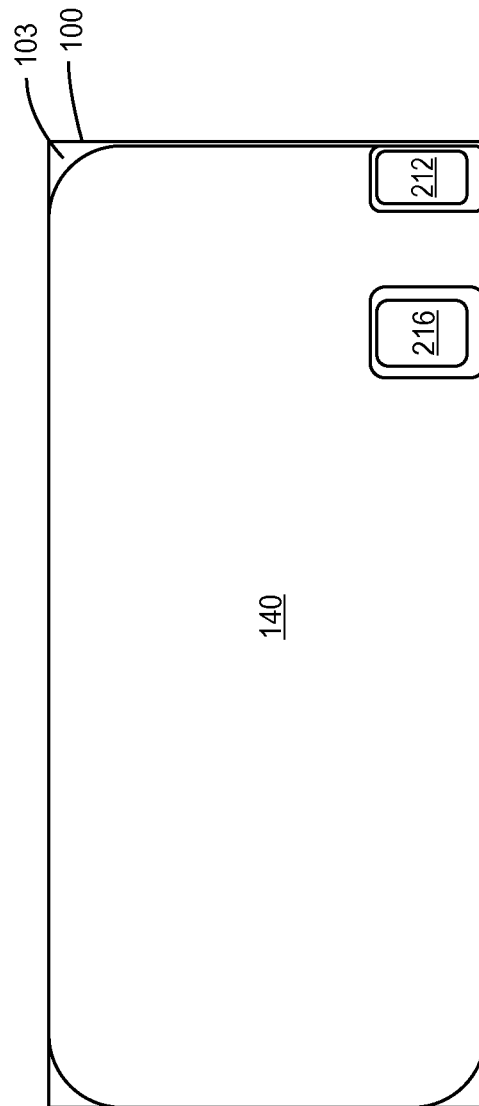


FIGURE 3B



**FIGURE 3C**

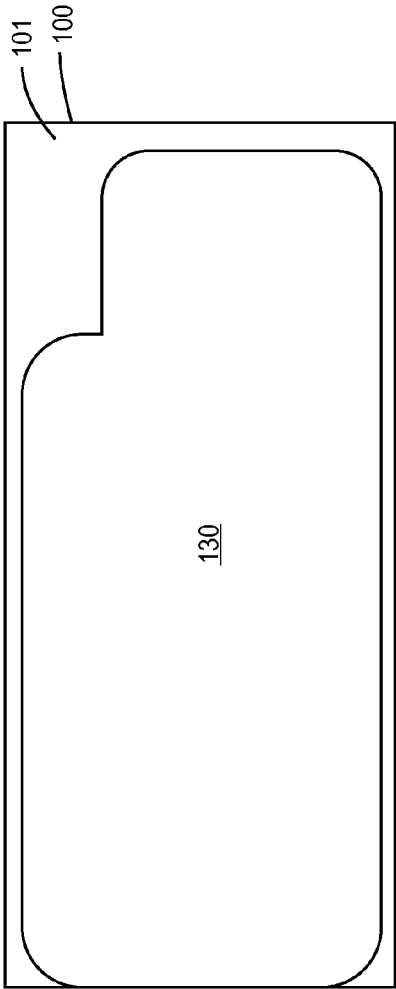


FIGURE 4A

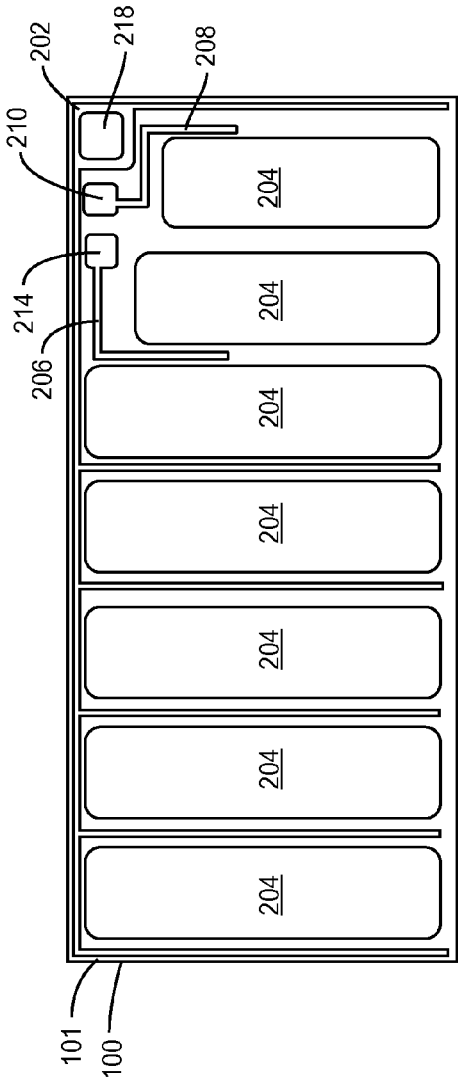


FIGURE 4B

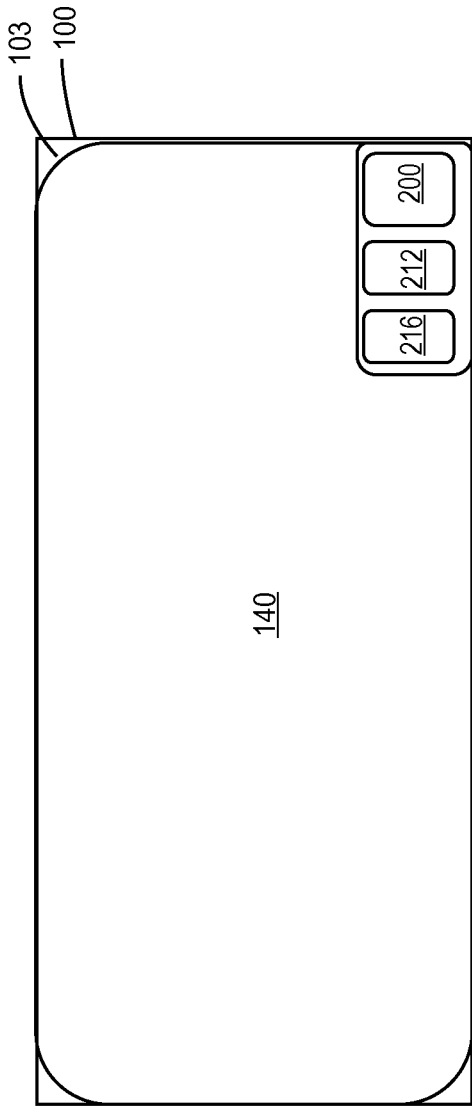


FIGURE 4C

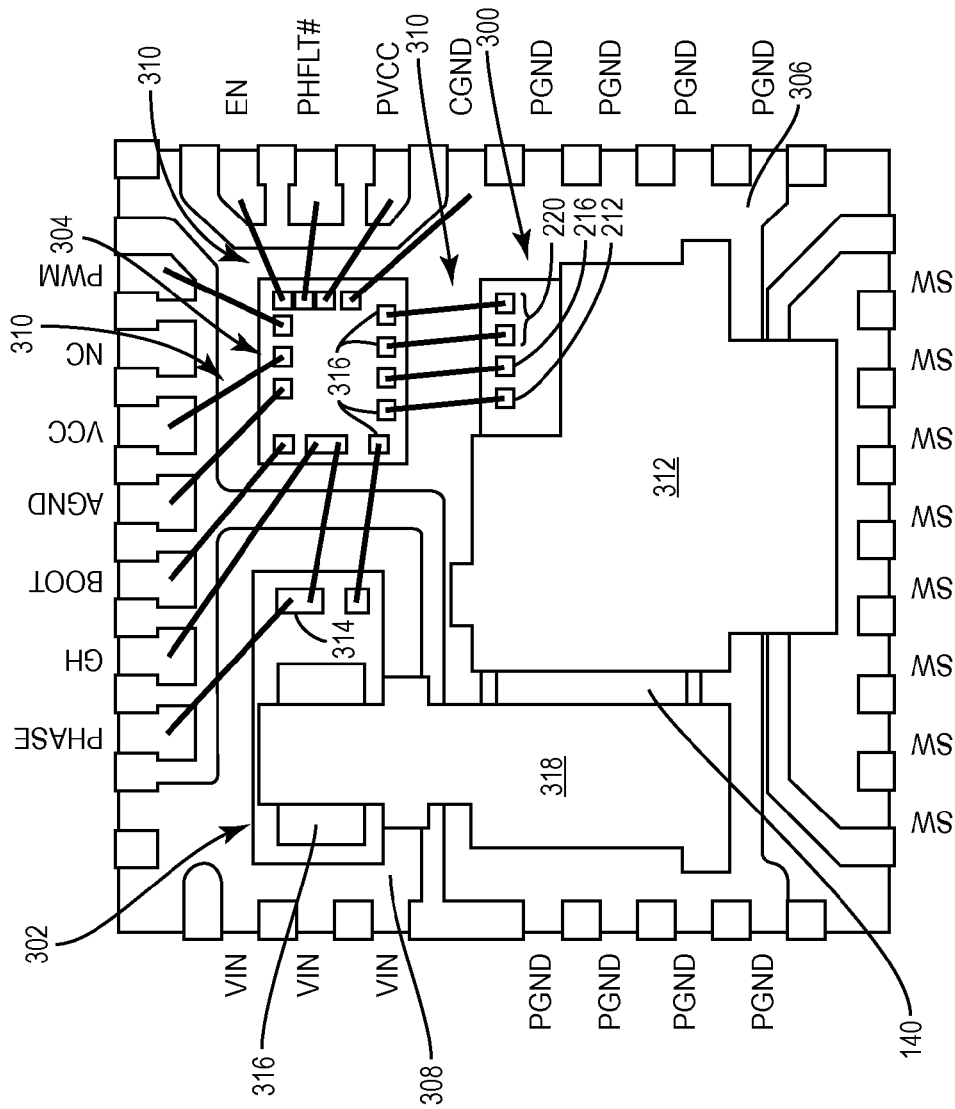


FIGURE 5

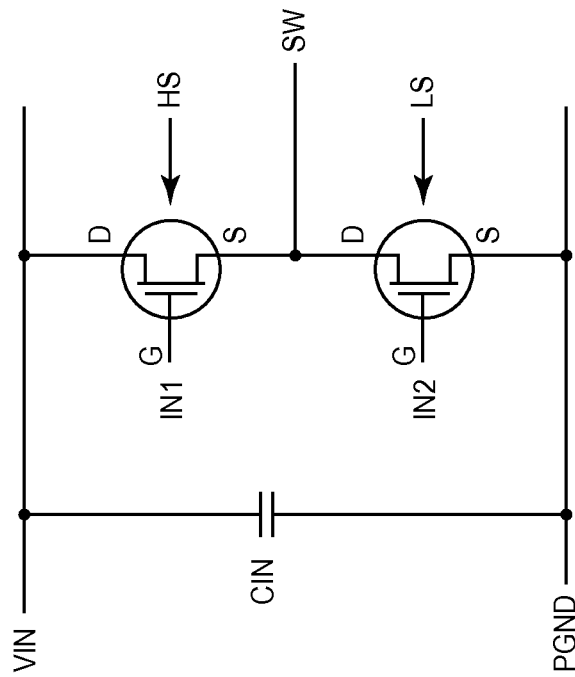


FIGURE 6

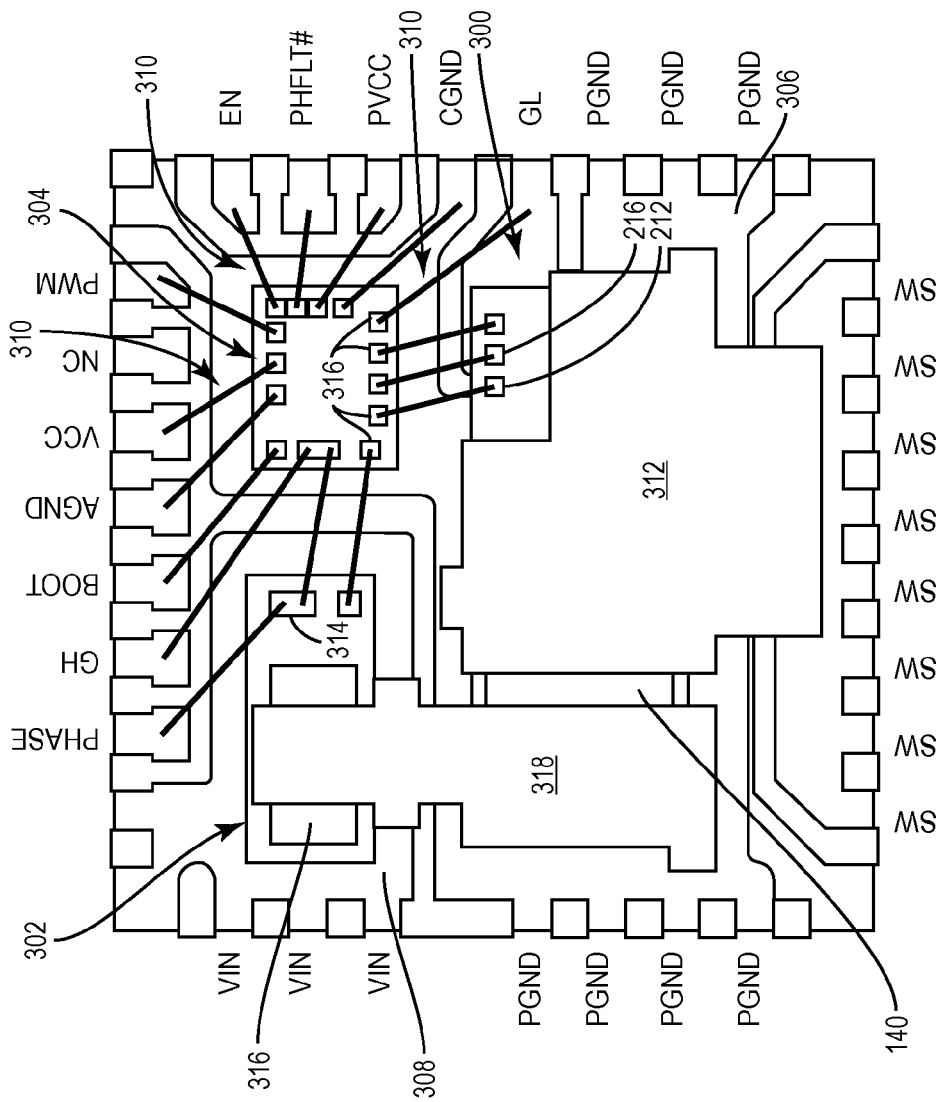


FIGURE 7

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# SEMICONDUCTOR DIE AND PACKAGE WITH SOURCE DOWN AND SENSING CONFIGURATION

## TECHNICAL FIELD

The instant application relates to semiconductor dies and corresponding packages, and more particularly to semiconductor dies with sensing and corresponding packages.

## BACKGROUND

The drain of a conventional vertical power transistor die is directly connected to a die pad at the backside of the die. The drain pad of the die is directly connected to a drain lead of the package. In many applications, it is desirable to sense the transistor source current or temperature. Conventional techniques for sensing source current or temperature typically involve providing a dedicated sense pad separate from the source pad at the front side of the transistor die. The front side of the die is flipped during the die bond process, and the dedicated source pad is directly soldered or glued. Such a die/package configuration requires a dedicated die pad design for related sensing redistribution, increasing package design complexity and package cost.

## SUMMARY

According to an embodiment of a semiconductor die, the semiconductor die comprises a semiconductor body. A transistor device is disposed in the semiconductor body. The transistor device has a gate, a source and a drain. A sense device is also disposed in the semiconductor body. The sense device is operable to sense a parameter associated with the transistor device e.g. such as temperature or source current. A source pad at a first side of the semiconductor body is electrically connected to the source of the transistor device. A drain pad at a second side of the semiconductor body opposing the first side is electrically connected to the drain of the transistor device. A sense pad at the second side of the semiconductor body and spaced apart from the drain pad is electrically connected to the sense device.

According to an embodiment of a method of manufacturing a semiconductor die, the method comprises: forming a transistor device in a semiconductor body, the transistor device having a gate, a source and a drain; forming a sense device in the semiconductor body, the sense device operable to sense a parameter associated with the transistor device; forming a source pad at a first side of the semiconductor body, a drain pad at a second side of the semiconductor body opposing the first side, and a sense pad at the second side of the semiconductor body spaced apart from the drain pad; electrically connecting the source pad to the source of the transistor device; electrically connecting the drain pad to the drain of the transistor device; and electrically connecting the sense pad to the sense device.

According to an embodiment of a semiconductor package, the package comprises a first die paddle and a semiconductor die. The semiconductor die comprises a semiconductor body having a first side facing the first die paddle and a second side facing away from the first die paddle. A transistor device disposed in the semiconductor body has a gate, a source and a drain. A sense device also disposed in the semiconductor body is operable to sense a parameter associated with the transistor device. A source pad at the first side of the semiconductor body is attached to the first die paddle and electrically connected to the source of the transistor device. A drain

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pad at the second side of the semiconductor body opposing the first side is electrically connected to the drain of the transistor device. A sense pad at the second side of the semiconductor body and spaced apart from the drain pad is electrically connected to the sense device.

Those skilled in the art will recognize additional features and advantages upon reading the following detailed description, and upon viewing the accompanying drawings.

## BRIEF DESCRIPTION OF THE DRAWINGS

The components in the figures are not necessarily to scale, emphasis instead being placed upon illustrating the principles of the invention. Moreover, in the figures, like reference numerals designate corresponding parts. In the drawings:

FIG. 1 illustrates a cross-sectional view of an embodiment of a semiconductor die with a source-down and sensing configuration;

FIG. 2 illustrates a cross-sectional view of another embodiment of a semiconductor die with a source-down and sensing configuration;

FIGS. 3A through 3C illustrate different perspective views of a semiconductor die with a source-down and sensing configuration according to a first embodiment;

FIGS. 4A through 4C illustrate different perspective views of a semiconductor die with a source-down and sensing configuration according to a second embodiment;

FIG. 5 illustrates a top plan view of an embodiment of a semiconductor package including a semiconductor die with a source-down and sensing configuration;

FIG. 6 illustrates a circuit schematic of an exemplary half-bridge circuit; and

FIG. 7 illustrates a top plan view of another embodiment of a semiconductor package including a semiconductor die with a source-down and sensing configuration.

## DETAILED DESCRIPTION

Embodiments described herein provide a power semiconductor die with a source-down configuration in which the source pad of the die is attached to a die paddle of a package, and the drain pad and a dedicated sense pad are provided at the opposite side of the die. A conductive via can be used to electrically connect the sense device, which can be disposed at the same side of the die as the source of the power transistor, to the dedicated sense pad at the opposite (drain) side of the die. The source-down semiconductor die embodiments described herein reduce switching losses, thereby lowering static losses.

FIG. 1 illustrates a partial cross-sectional view of a semiconductor die according to an embodiment. The die includes a semiconductor body 100. The semiconductor body 100 can be made of any semiconductor material suitable for manufacturing a semiconductor device. Examples of such materials include, without being limited thereto, elementary semiconductor materials such as silicon (Si) or germanium (Ge), group IV compound semiconductor materials such as silicon carbide (SiC) or silicon germanium (SiGe), binary, ternary or quaternary III-V semiconductor materials such as gallium nitride (GaN), gallium arsenide (GaAs), gallium phosphide (GaP), indium phosphide (InP), indium gallium phosphide (InGaP), aluminum gallium nitride (AlGaN), aluminum indium nitride (AlInN), indium gallium nitride (InGaN), aluminum gallium indium nitride (AlGaInN) or indium gallium arsenide phosphide (InGaAsP), and binary or ternary II-VI semiconductor materials such as cadmium telluride (CdTe) and mercury cadmium telluride (HgCdTe), to name few.

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A transistor device and a sense device are both disposed in the semiconductor body **100**. The transistor device has a gate **102**, a source **104** and a drain **106**. The source **104** is disposed in and separated from a drift region **108** of the transistor device by a body region **110** of the opposite conductivity type. The gate **102** of the transistor device is separated from the surrounding semiconductor material by an insulating material **112** such as SiO<sub>2</sub>. The transistor device is a trench device according to this embodiment in that the gate **102** is disposed in a trench **114**. A field plate **116** separated from the gate **102** by the trench insulating material **112** can be disposed in the trench **114** below the gate **102**. Alternatively, the gate **102** can be formed on the top side **101** of the semiconductor body **100** in a planar gate arrangement. In each case, the sense device is operable to sense a parameter associated with the transistor device such as temperature or source current of the transistor device. In one embodiment the sense device is a scaled, smaller version of the transistor device and the corresponding regions of the sense device have the same reference numbers in the Figures as the transistor device with the addition of an apostrophe (').

The semiconductor die further includes a source pad **130** at a first (top) side **101** of the semiconductor body **100**, and a drain pad **140** and a dedicated sense pad **150** at a second (bottom) side **103** of the semiconductor body **100** opposing the first side **101**. The source pad **130** is electrically connected to the source **104** of the transistor device and the drain pad **140** is electrically connected to the drain **106** of the transistor device. The sense pad **150** is spaced apart from the drain pad **140** at the bottom side **103** of the die, and is electrically connected to the sense device.

In the embodiment shown in FIG. 1, the transistor device is a vertical transistor device. The source **104** is disposed at the top side **101** of the semiconductor body **100** and the drain **106** is disposed at the bottom side **103** of the semiconductor body **100**. The source pad **130** is electrically connected to the source **104** at the top side **101** of the semiconductor body **100** by conductive vias (out of view in FIG. 1) which extend from the source pad **130** to the source **104** of the transistor device through an interlayer dielectric layer **160**. The drain pad **140** is connected to the drain **106** of the transistor device at the bottom side **103** of the semiconductor body **100**. Current flows in the vertical direction through the semiconductor body **100** between the source and drain **104**, **106** according to this embodiment. A passivation layer **162** such as an imide can be provided on the semiconductor body **100** at the top side **101**. A source metal redistribution layer **164** is connected to the source **104** of the main transistor device by conductive vias **166** which extend through the interlayer dielectric layer **160** separating the source metal redistribution layer **164** from the semiconductor body **100**.

In one embodiment, the sense pad **150** is electrically connected to the source **104'** of the sense device and the sense device senses the source current of the main transistor device. According to this embodiment, the die includes a source sense metal redistribution layer **170** connected to the source **104'** of the sense device by conductive vias **172**. The conductive vias **172** extend through the interlayer dielectric layer **160** which separates the sense redistribution layer **170** from the semiconductor body **100**.

The source sense metal redistribution layer **170** of the sense device can be electrically connected at the top side **101** of the semiconductor body **100** to the sense pad **150** at the bottom side **103** of the semiconductor body **100** by a first conductive via **180** which extends into the semiconductor body **100** from the top side **101**. The first conductive via **180** is aligned with and extends toward the sense pad **150** at the second side **103**

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of the semiconductor body **100**. The semiconductor body **100** has a certain thickness (T<sub>body</sub>), and the first conductive via **180** extends to a depth (D<sub>via</sub>) in the semiconductor body **100** that is less than the thickness of the body **100**. As such, the first conductive via **180** is spaced apart from the sense pad **150** in the vertical direction by a highly doped region **107** of the semiconductor body **100**. The vertical direction is generally perpendicular to the main sides **101**, **103** of the semiconductor body **100**. The source sense metal redistribution layer **170** of the sense device is connected to the first conductive via **180** by a conductive via **182** that extends through the interlayer dielectric layer **160** which separates the sense redistribution layer **170** from the semiconductor body **100**. The sense pad **150** is electrically connected to the source sense metal redistribution layer **170** of the sense device at the top side **101** of the semiconductor body **100** by the first conductive via **180** and the highly doped region **107** of the semiconductor body **100** interposed between the first conductive via **180** and the sense pad **150**. The sides **181** of the first conductive via **180** can be insulated from the surrounding semiconductor material by an insulating material **184** such as an oxide. In one embodiment, the semiconductor body **100** comprises silicon and the first conductive via **180** is a so-called silicon through via comprising polysilicon or metal.

At least one additional conductive via **190** can be provided which extends through the semiconductor body **100** from the first side **101** to the second side **103** and is spaced apart from the first conductive via **180**. The additional conductive via(s) **190** extend over the entire thickness (T<sub>body</sub>) of the semiconductor body **100**, and are insulated from the surrounding semiconductor material by an insulating material **192** such as an oxide. The additional conductive via(s) **190** provide device isolation. To this end, the additional conductive via(s) **190** can be connected to the sense redistribution layer **170** at the top side **101** of the semiconductor body **100** through conductive vias **194** extending through the interlayer dielectric layer **160**. In one embodiment, the semiconductor body **100** comprises silicon and the additional conductive via(s) **190** are so-called silicon through vias comprising polysilicon or metal.

In the embodiment shown in FIG. 1, the sense pad **150** is insulated from the additional conductive via(s) **190** at the second side **103** of the semiconductor body **100** by an insulating material **196** such as an oxide. The insulating material **196** also separates the sense pad **150** from the drain pad **140**. FIG. 2 illustrates a partial cross-sectional view of a semiconductor die according to another embodiment. The embodiment shown in FIG. 2 is similar to the embodiment shown in FIG. 1, however the sense pad **150** at the bottom side **103** of the semiconductor body **101** also contacts the additional conductive via(s) **190** at the bottom side **103** of the body **100**.

FIGS. 3A through 3C illustrate different perspective views of the semiconductor die shown in FIG. 1 or 2. FIG. 3A illustrates a top plan view of the semiconductor die, FIG. 3B shows the top plan view without die pads and interlayer dielectrics, and FIG. 3C shows a bottom plan view of the semiconductor die. According to this embodiment, a gate pad **200** is provided at the top side of the semiconductor body **100** and spaced apart from the source pad **130**. The gate pad **200** is electrically connected to the gate **102** of the main transistor device. In FIG. 3B, the gate pad is connected to a gate metal redistribution layer **202** which is separate (isolated) from the source sense metal redistribution layer **170** of the sense device. Electrical connections to the gate **102** of the main transistor device are formed by conductive vias (not shown for ease of illustration) which extend from the gate metal redistribution layer **202** to the transistor gate **102** through the

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interlayer dielectric layer **160** that separates the gate metal redistribution layer **202** from the semiconductor body **100**.

Also shown in FIG. 3B is the source metal redistribution layer **204** (region **164** in FIGS. 1 and 2) which is connected to the source **104** of the main transistor device by conductive vias (region **172** in FIGS. 1 and 2) which extend from the source metal redistribution layer **204** to the transistor source **104** through the interlayer dielectric layer **160**. Also shown are a sensing line **206** and a tapping line **208** of the sense device. In the case of the sense device being a scaled and smaller version of the transistor device and the sense device being operable to sense the source current of the transistor device, the sensing line **206** is connected to the source **104'** of the smaller sense transistor and the tapping line **208** is connected to the source potential of the larger main transistor device. The sensing line **206** can have the same or similar construction as the source sense metal redistribution layer **170** shown in FIGS. 1 and 2. The tapping line **208** can have the same or similar construction as the sensing line **206**, except the tapping line is connected to the source potential of the main transistor device instead of the source **104'** of the sense device.

A first conductive via **210** extends into the semiconductor body **100** from the top side **101** toward a first sense pad **212** at the bottom side **103** of the semiconductor body **100** as shown in FIG. 3C. The first conductive via **210** can have the same or similar construction as via **180** shown in FIGS. 1 and 2, and the first sense pad **212** can have the same or similar construction as sense pad **150** shown in FIGS. 1 and 2. The first sense pad **212** is electrically connected to the tapping line **208** by the first conductive via **210** and the highly doped region of the semiconductor body **100** vertically interposed between the first conductive via **210** and the first sense pad **212** as previously described herein.

A second conductive via **214** similarly extends into the semiconductor body **100** from the top side **101** toward a second sense pad **216** at the bottom side **103** of the semiconductor body **100** as shown in FIG. 3C. The second conductive via **214** can have the same or similar construction as via **180** shown in FIGS. 1 and 2, and the first sense pad **212** can have the same or similar construction as sense pad **150** shown in FIGS. 1 and 2. The second sense pad **216** is electrically connected to the sensing line **206** by the second conductive via **214** and the highly doped region of the semiconductor body **100** vertically interposed between the second conductive via **214** and the second sense pad **216** as previously described herein. The die pad **140** and the sense pads **212**, **216** are isolated from one another at the bottom side **103** of the semiconductor body **100** e.g. by a passivation layer such as an imide which is not shown in FIG. 3C for ease of illustration (see for example layer **196** in FIGS. 1 and 2).

FIGS. 4A through 4C illustrate different perspective view of the semiconductor die shown in FIG. 1 or 2, according to yet another embodiment. FIG. 4A illustrates a top plan view of the semiconductor die, FIG. 4B shows the top plan view without die pads and interlayer dielectrics, and FIG. 4C shows a bottom plan view of the semiconductor die. The embodiment shown in FIGS. 4A through 4C is similar to the embodiment shown in FIGS. 3A through 3C, however the gate pad **200** is provided at the bottom side **103** of the semiconductor body **100** with the drain pad **140** and sense pads **212**, **216** instead of at the top side **101** of the semiconductor body **100** with the source pad **130**. To this end, an additional conductive via **218** is provided for connecting gate metal redistribution layer **202** at the top side **101** of the semiconductor body **100** with the gate pad **200** at the bottom side **103** of the semiconductor body **100** as shown in FIGS. 4B and 4C.

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According to this embodiment, only the source pad **130** is disposed at the top side **101** of the semiconductor body **100** as shown in FIG. 4A. The drain pad **140**, gate pad **200** and sense pads **212**, **216** are each provided at the bottom side **103** of the semiconductor body **100** and isolated from one another e.g. by a passivation layer such as an imide which is not shown in FIG. 4C for ease of illustration (see for example layer **196** in FIGS. 1 and 2).

A method of manufacturing the semiconductor dies described herein comprises: forming a transistor device in a semiconductor body, the transistor device having a gate, a source and a drain; forming a sense device in the semiconductor body, the sense device operable to sense a parameter associated with the transistor device; forming a source pad at a first side of the semiconductor body, a drain pad at a second side of the semiconductor body opposing the first side, and a sense pad at the second side of the semiconductor body spaced apart from the drain pad; electrically connecting the source pad to the source of the transistor device; electrically connecting the drain pad to the drain of the transistor device; and electrically connecting the sense pad to the sense device.

The sense pad can be electrically connected to the sense device by forming a first conductive via extending into the semiconductor body from the first side and spaced apart from the sense pad by a highly doped region of the semiconductor body. The sense pad is electrically connected to the sense device by the first conductive via and the highly doped region of the semiconductor body interposed between the first conductive via and the sense pad.

An additional sense pad can be formed at the second side of the semiconductor body and spaced apart from the other sense pad and the drain pad. The additional sense pad can be electrically connected to the source of the transistor device, e.g., by forming a conductive via extending into the semiconductor body from the first side and spaced apart from the additional sense pad by a highly doped region of the semiconductor body. The additional sense pad is electrically connected to the source of the transistor device by the conductive via and the highly doped region of the semiconductor body interposed between the conductive via and the additional sense pad.

The semiconductor dies described herein can be assembled into a package. When assembling the semiconductor die into a package, the source-side of the die is placed face down in the package so that the pad is attached to a die paddle of the package. The drain pad and sense pads face away from the die paddle. The gate pad can be at the source-side or drain-side of the die as previously described herein.

FIG. 5 illustrates a top plan view of a semiconductor package which includes the semiconductor die **300** shown in FIGS. 4A through 4C and additional semiconductor dies **302**, **304**. For ease of explanation and illustration only certain package parts such as a lid and mold compound or other encapsulating material are not shown, and the circuit realized by the components included in the package of FIG. 5 is a half-bridge converter circuit as shown in FIG. 6. The half-bridge circuit includes a low-side transistor (LS) corresponding to die **300**, a high-side transistor (HS) die corresponding to die **302** and an input capacitor (C<sub>in</sub>) coupled between the positive input (VIN) and the negative input (PGND) of the half-bridge circuit. The negative input can be ground in some configurations. The low-side transistor LS corresponds to the semiconductor die **300** shown in FIGS. 4A through 4C in that the gate pad **200** and source pad **130** are disposed at the same side of the die **300**. In the exemplary circuit diagram shown in FIG. 6, the transistors are MOSFETs each having gate (G), drain (D) and source (S) terminals.

The gate, drain and source terminals of the low-side transistor LS correspond to the gate, drain and source pads **200**, **140**, **130** shown in FIGS. 4A through 4C, respectively. The drain terminal of the high-side transistor HS is electrically connected to the positive input (VIN) of the half-bridge circuit. The source terminal of the high-side transistor HS is electrically connected to the drain terminal of the low-side transistor LS to form the output (SW) of the half-bridge circuit. The source terminal of the low-side transistor LS is electrically connected to the negative input (PGND). The transistor gates (G) serve as control signal inputs (IN1, IN2). IGBTs can be used instead of MOSFETs where the collector connections of the IGBTs would correspond to the drain connections of the MOSFETs and the emitter connections of the IGBTs would correspond to the source connections of the MOSFETs. The package also includes a controller die **304** with various (signal and power) inputs and outputs (e.g., PHASE, GL, BOOT, AGND, VCC, PWM, EN, PHFLT#, PVCC, CGND, GL) for controlling operation of the half-bridge circuit. In general the type and number of semiconductor dies included in the package depends on the particular application for which the package is designed, and the inter-die interconnect embodiments described herein can be used in each case.

The package also includes a first die paddle **306** and a second die paddle **308**. The source pad **130** of the low-side transistor die **300** is attached to the first die paddle **306** and electrically connected to the source terminal of the low-side transistor LS included in the die **300**. The controller die **304** also has a pad facing and connected to the first die paddle **306**. The drain pad **140** of the low-side transistor die **300** is disposed at the opposite side of the die **300** facing away from the first die paddle **306**. The drain pad **140** is electrically connected to the drain (D) of the low-side transistor. The sense pads **212**, **216** and gate pad **300** are disposed at the same side of the die **300** as the drain pad **140**, and spaced apart from the drain pad **140**. Hence only the source pad **130** of the low-side transistor die **300** faces the first die paddle **306**. Bond wire connections **310** connect the gate and sense pads **200**, **212**, **216** of the low-side transistor die **300** to the controller die **304**. The drain pad **140** of the low-side transistor die **300** is connected to an output lead (SW) of the package by a metal clip **312**.

The drain pad (out of view) of the high-side transistor die **302** is connected to the second die paddle **308** of the package. Bond wire connections **310** are provided between the gate pad **314** of the high-side transistor die **302** and one or more corresponding pads **316** of the controller die **304**. Bond wire connections **310** are also provided between various leads of the package and the dies **300**, **302**, **304**. The source pad **316** of the high-side transistor die **302** faces away from the second die paddle **308** and is connected to the drain pad **140** of the low-side transistor die **300** by a metal clip **318** to form the half-bridge circuit connections shown in FIG. 6 (the input capacitor Cin is omitted from FIG. 5 for ease of illustration). The gate pad **200** of the low-side transistor die **300** is disposed at the same side of the die **300** as the drain and sense pads **140**, **212**, **216** according to the embodiment of FIG. 6. As such, the gate pad **200** of the low-side transistor die **300** faces away the first die paddle **306**. The gate pad **200** of the low-side transistor die **300** is connected to a corresponding pad **316** of the controller die **304** by one or more bond wire connections **310**.

FIG. 7 illustrates a top plan view of another embodiment of a semiconductor package which is similar to the embodiment shown in FIG. 5, however the low-side transistor die **300** corresponds to the semiconductor die shown in FIGS. 3A through 3C instead of FIGS. 4A through 4C. The gate pad **200**

of the low-side transistor die **300** is disposed at the same side of the die as the source pad **130** according to this embodiment. As such, the gate pad **200** of the low-side transistor die faces toward the first die paddle **306** according to this embodiment. The gate pad **200** is spaced apart from the source pad **130** and attached to a lead (GL) of the package in the same plane as the first die paddle **306**. In both FIG. 5 and FIG. 7, the low-side transistor die is attached to the die paddle of the package in a source-down configuration with sensing.

Spatially relative terms such as “under”, “below”, “lower”, “over”, “upper” and the like, are used for ease of description to explain the positioning of one element relative to a second element. These terms are intended to encompass different orientations of the device in addition to different orientations than those depicted in the figures. Further, terms such as “first”, “second”, and the like, are also used to describe various elements, regions, sections, etc. and are also not intended to be limiting. Like terms refer to like elements throughout the description.

As used herein, the terms “having”, “containing”, “including”, “comprising” and the like are open-ended terms that indicate the presence of stated elements or features, but do not preclude additional elements or features. The articles “a”, “an” and “the” are intended to include the plural as well as the singular, unless the context clearly indicates otherwise.

With the above range of variations and applications in mind, it should be understood that the present invention is not limited by the foregoing description, nor is it limited by the accompanying drawings. Instead, the present invention is limited only by the following claims and their legal equivalents.

What is claimed is:

1. A semiconductor die, comprising:

- a semiconductor body;
- a transistor device disposed in the semiconductor body and having a gate, a source and a drain;
- a sense device disposed in the semiconductor body and operable to sense a parameter associated with the transistor device;
- a source pad at a first side of the semiconductor body and electrically connected to the source of the transistor device;
- a drain pad at a second side of the semiconductor body opposing the first side and electrically connected to the drain of the transistor device;
- a sense pad at the second side of the semiconductor body and spaced apart from the drain pad, the sense pad electrically connected to the sense device; and
- a gate pad at one of the first side or the second side of the semiconductor body, the gate pad being electrically connected to the gate of the transistor device, the gate pad being spaced apart from the sense pad and the drain pad if disposed at the second side, the gate pad being spaced apart from the source pad if disposed at the first side.

2. The semiconductor die of claim 1, wherein the transistor device is a vertical transistor device, the source is disposed at the first side of the semiconductor body, the drain is disposed at the second side of the semiconductor body, the source pad is connected to the source at the first side of the semiconductor body, and the drain pad is connected to the drain at the second side of the semiconductor body.

3. The semiconductor die of claim 1, further comprising a first conductive via extending into the semiconductor body from the first side and spaced apart from the sense pad by a highly doped region of the semiconductor body, wherein the sense pad is electrically connected to the sense device by the

first conductive via and the highly doped region of the semiconductor body interposed between the first conductive via and the sense pad.

4. The semiconductor die of claim 3, further comprising at least one additional conductive via extending through the semiconductor body from the first side to the second side and spaced apart from the first conductive via.

5. The semiconductor die of claim 4, wherein the sense pad contacts the at least one additional conductive via at the second side of the semiconductor body.

6. The semiconductor die of claim 4, wherein the sense pad is insulated from the at least one additional conductive via at the second side of the semiconductor body.

7. The semiconductor die of claim 3, further comprising: an insulating layer on the first side of the semiconductor body;

a metal layer on the insulating layer; and

a conductive via extending through the insulating layer and electrically connecting the metal layer to the first conductive via.

8. The semiconductor die of claim 7, wherein the source pad is connected to the metal layer and the sense device is operable to sense current at the source of the transistor device.

9. The semiconductor die of claim 3, wherein the semiconductor body comprises silicon and the first conductive via comprises polysilicon or metal.

10. The semiconductor die of claim 1, further comprising an additional sense pad at the second side of the semiconductor body and spaced apart from the other sense pad and the drain pad, the additional sense pad electrically connected to the source of the transistor device.

11. The semiconductor die of claim 10, further comprising a conductive via extending into the semiconductor body from the first side and spaced apart from the additional sense pad by a highly doped region of the semiconductor body, wherein the additional sense pad is electrically connected to the source of the transistor device by the conductive via and the highly doped region of the semiconductor body interposed between the conductive via and the additional sense pad.

12. A method of manufacturing a semiconductor die, the method comprising:

forming a transistor device in a semiconductor body, the transistor device having a gate, a source and a drain;

forming a sense device in the semiconductor body, the sense device operable to sense a parameter associated with the transistor device;

forming a source pad at a first side of the semiconductor body, a drain pad at a second side of the semiconductor body opposing the first side, and a sense pad at the second side of the semiconductor body spaced apart from the drain pad;

forming a gate pad at one of the first side or the second side of the semiconductor body, the gate pad being spaced apart from the sense pad and the drain pad if disposed at the second side, the gate pad being spaced apart from the source pad if disposed at the first side;

electrically connecting the gate pad to the gate of the transistor device;

electrically connecting the source pad to the source of the transistor device;

electrically connecting the drain pad to the drain of the transistor device; and

electrically connecting the sense pad to the sense device.

13. The method of claim 12, wherein electrically connecting the sense pad to the sense device comprises:

forming a first conductive via extending into the semiconductor body from the first side and spaced apart from the

sense pad by a highly doped region of the semiconductor body, the sense pad being electrically connected to the sense device by the first conductive via and the highly doped region of the semiconductor body interposed between the first conductive via and the sense pad.

14. The method of claim 12, further comprising:

forming an additional sense pad at the second side of the semiconductor body and spaced apart from the other sense pad and the drain pad; and

electrically connecting the additional sense pad to the source of the transistor device.

15. The method of claim 14, wherein electrically connecting the additional sense pad to the source of the transistor device comprises:

forming a conductive via extending into the semiconductor body from the first side and spaced apart from the additional sense pad by a highly doped region of the semiconductor body, the additional sense pad being electrically connected to the source of the transistor device by the conductive via and the highly doped region of the semiconductor body interposed between the conductive via and the additional sense pad.

16. A semiconductor package, comprising:

a first die paddle; and

a semiconductor die comprising:

a semiconductor body having a first side facing the first die paddle and a second side facing away from the first die paddle;

a transistor device disposed in the semiconductor body and having a gate, a source and a drain;

a sense device disposed in the semiconductor body and operable to sense a parameter associated with the transistor device;

a source pad at the first side of the semiconductor body, the source pad attached to the first die paddle and electrically connected to the source of the transistor device;

a drain pad at the second side of the semiconductor body opposing the first side and electrically connected to the drain of the transistor device; and

a sense pad at the second side of the semiconductor body and spaced apart from the drain pad, the sense pad electrically connected to the sense device.

17. The semiconductor package of claim 16, further comprising an additional sense pad at the second side of the semiconductor body and spaced apart from the other sense pad and the drain pad, the additional sense pad electrically connected to the source of the transistor device.

18. The semiconductor package of claim 16, further comprising a gate pad at the second side of the semiconductor body and spaced apart from the sense pad and the drain pad, the gate pad electrically connected to the gate of the transistor device.

19. The semiconductor package of claim 16, further comprising:

an electrically conductive lead in the same plane as the first die paddle; and

a gate pad at the first side of the semiconductor body and spaced apart from the source pad, the gate pad attached to the lead and electrically connected to the gate of the transistor device.

20. The semiconductor package of claim 16, wherein the semiconductor die is a low-side power transistor die of a half-bridge circuit, the semiconductor package further comprising:

a controller die having a first pad attached to the first die paddle and a plurality of additional pads at a side of the

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controller die facing away from the first die paddle, the  
controller die operable to control operation of the half-  
bridge circuit;  
a second die paddle spaced apart from the first die paddle;  
and  
a high-side power transistor die of the half-bridge circuit,  
the high-side power transistor die having a drain pad  
attached to the second die paddle, a gate pad electrically  
connected to a first one of the additional terminals of the  
controller die, and a source pad electrically connected to  
the drain pad of the low-side power transistor die.

\* \* \* \* \*

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UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**


PATENT NO. : 9,123,701 B2  
APPLICATION NO. : 13/939894  
DATED : September 1, 2015  
INVENTOR(S) : Otremba et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page/Inventors (72) line 3, please change "Martin Pölzi" to -- Martin Pölzl --

Signed and Sealed this  
Third Day of May, 2016

A handwritten signature in black ink, reading "Michelle K. Lee". The signature is fluid and cursive, with the first letters of each name being capitalized and prominent.

Michelle K. Lee  
*Director of the United States Patent and Trademark Office*